BLC8G27LS-180AV

Power LDMOS transistor

AMPLEON

Rev. 5 — 24 May 2017

Product data sheet

1. Product profile

1.1 General description

180 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2496 MHz to 2690 MHz.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C in a Doherty production test circuit.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	η_D	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2496 to 2690	28	28	14	43.5	-30 <u>[1]</u>

^[1] Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- High efficiency
- Excellent ruggedness
- Designed for broadband operation
- Low thermal resistance providing excellent thermal stability
- Integrated ESD protection
- Designed for low memory effects providing excellent pre-distortability
- Lower output capacitance for improved performance in Doherty applications
- Asymmetrical design to achieve optimal efficiency across the band
- Decoupling leads to enable improved video bandwidth
- Internally matched for ease of use (input and output)
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

■ RF power amplifier for W-CDMA base stations and multi carrier applications in the 2496 MHz to 2690 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)		5 1 2 6	1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC8G27LS-180AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j\text{-case})}$		T_{case} = 80 °C; V_{DS} = 28 V; I_{Dq} = 200 mA; $V_{GS(amp)peak}$ = 0.6 V; f = 2600 MHz; P_L = 28 W	0.38	K/W

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice				1	
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.7 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 72 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 300 mA	1.6	2.0	2.4	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.2	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	13.3	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	120	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 72 mA	-	0.63	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.52 \text{ A}$	-	198	318	mΩ
Peak dev	rice					_
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.3 \text{ mA}$	65	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 130 mA	1.5	1.9	2.3	V
V_{GSq}	gate-source quiescent voltage	V _{DS} = 28 V; I _D = 600 mA	1.6	2.0	2.4	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.2	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	23	-	Α
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	120	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 130 mA	-	1.13	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 4.55 \text{ A}$	-	109	155	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2496 MHz; f_2 = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.6 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 28 W	13	14	-	dB
RLin	input return loss	P _{L(AV)} = 28 W	-	-10	-7	dB
η_{D}	drain efficiency	P _{L(AV)} = 28 W	39.5	43.5	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 28 W	-	-30	-26	dBc

Table 8. RF characteristics

Test signal: pulsed CW; t_p = 100 μ s; δ = 10 %; f = 2690 MHz; RF performance at V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.6 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at 2496 MHz to 2690 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
L(GGD)	output power at 3 dB gain compression		153	173	193	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC8G27LS-180AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 28 V; I_{Dq} = 200 mA (main); $V_{GS(amp)peak}$ = 0.6 V; P_L = 140 W; f = 2496 MHz.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 420 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum po	Maximum power load									
2496	3.1 – j7.4	2.7 – j7.7	49.4	56.4	14.7					
2600	4.0 – j7.7	2.7 – j8.3	49.3	54.8	15.3					
2690	4.6 – j7.2	2.7 – j8.3	49.4	56	16.1					
Maximum dra	ain efficiency load									
2496	3.1 – j7.4	5.7 – j6.1	47.7	63.3	17					
2600	4.0 – j7.7	4.2 – j6.1	48.1	62.6	17.5					
2690	4.6 – j7.2	3.7 – j6.4	48.2	63	18.2					

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 780 mA (peak); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum pov	Maximum power load									
2496	3.9 – j8.9	3.9 – j10.8	51.7	55	14.2					
2600	5.3 – j9.3	4.7 – j12.0	51.6	52.4	14.6					
2690	6.3 – j7.6	6.0 – j12.4	51.3	54	15.6					
Maximum dra	in efficiency load									
2496	3.9 – j8.9	3.9 – j7.6	50.2	62.5	16.3					
2600	5.3 – j9.3	3.3 – j8.3	49.9	61.6	17					
2690	6.3 – j7.6	4.1 – j9.1	49.8	60.5	17.6					

^[1] Z_S and Z_L defined in Figure 1.

^[2] at 3 dB gain compression.

^[2] at 3 dB gain compression.

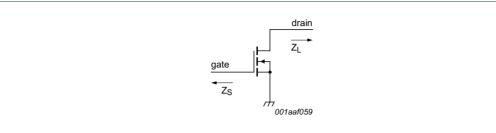


Fig 1. Definition of transistor impedance

7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load

Measured load-pull data of main device; I_{Dq} = 420 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	3.9 – j8.9	4.0 – j7.6	49.0	42	18.8
2600	5.3 – j9.3	3.9 – j7.5	48.9	41	19.0
2690	6.3 – j7.6	3.3 – j7.6	49.1	40	20.0

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

Table 12. Typical impedance of main device at 1:2 load

Measured load-pull data of main device; I_{Dq} = 420 mA (main); V_{DS} = 28 V.

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [3]	G _p [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2496	3.9 – j8.9	7.7 – j5.8	46.7	53.0	20.5
2600	5.3 – j9.3	7.0 – j5.1	46.5	52.0	21.0
2690	6.3 – j7.6	5.4 – j5.5	47.0	51.0	22.0

- [1] Z_S and Z_L defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at $P_{L(AV)} = 44.5 \text{ dBm}$.

7.4 VBW in Doherty operation

The BLC8G27LS-180AV shows 125 MHz (typical) video bandwidth in Doherty development board in 2600 MHz at V_{DS} = 28 V; I_{Dq} = 200 mA and $V_{GS(amp)peak}$ = 0.6 V.

7.5 Test circuit

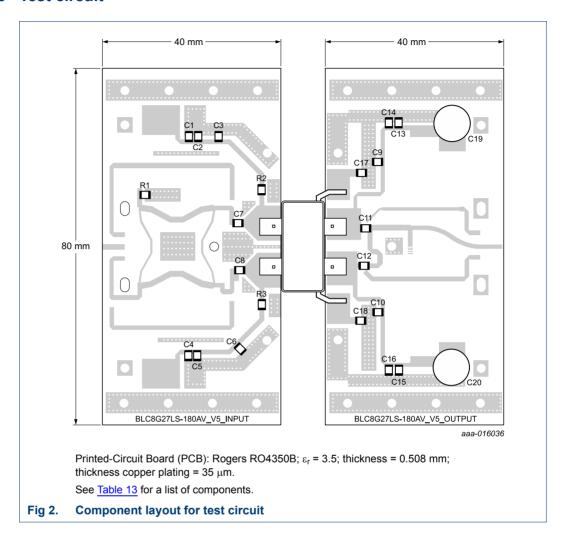


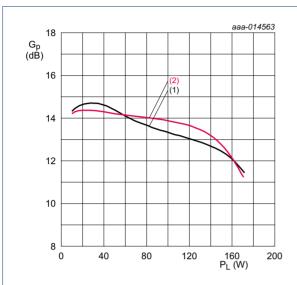
Table 13. List of components

See Figure 2 for component layout.

Component	Description	Value	Remarks
C1, C4, C13, C15, C17, C18	multilayer ceramic chip capacitor	10 μF, 50 V	Murata: SMD 1206
C2, C5, C14, C16	multilayer ceramic chip capacitor	1 μF, 50 V	Murata: SMD 1206
C3, C6, C7, C8, C9, C10, C12	multilayer ceramic chip capacitor	11 pF	ATC 600F series
C11	multilayer ceramic chip capacitor	3 pF	ATC 600F series
C19, C20	electrolytic capacitor	2200 μF, 63 V	Vishay BCcomponents
R1	SMD resistor	50 Ω	
R2, R3	SMD resistor	5.1 Ω	SMD 0805

7.6 Graphical data

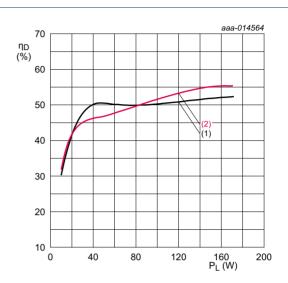
7.6.1 Pulsed CW



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

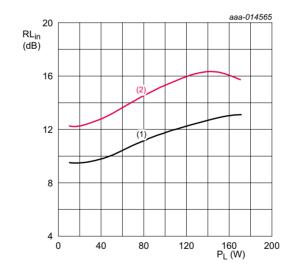
Fig 3. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V; t_p = 100 μ s; δ = 10 %.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 4. Drain efficiency as a function of output power; typical values

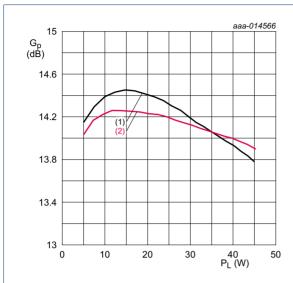


 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V; t_p = 100 μ s; δ = 10 %.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 5. Input return loss as a function of output power; typical values

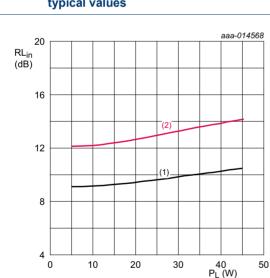
7.6.2 1-Carrier W-CDMA



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

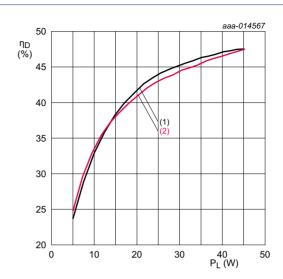
Fig 6. Power gain as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

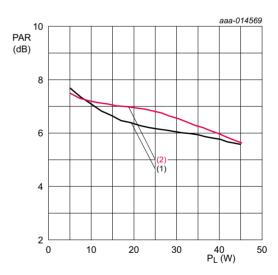
Fig 8. Input return loss as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

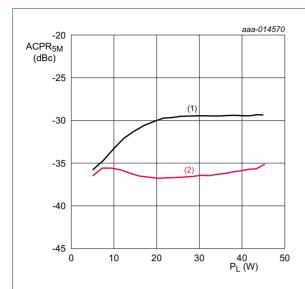
Fig 7. Drain efficiency as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

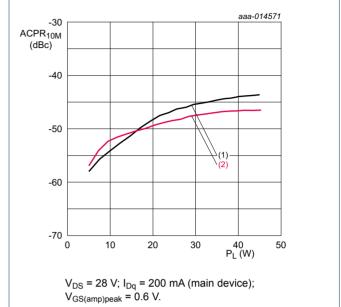
Fig 9. Peak-to-average power ratio as a function of output power; typical values



 V_{DS} = 28 V; I_{Dq} = 200 mA (main device); $V_{GS(amp)peak}$ = 0.6 V.

- (1) f = 2496 MHz
- (2) f = 2690 MHz

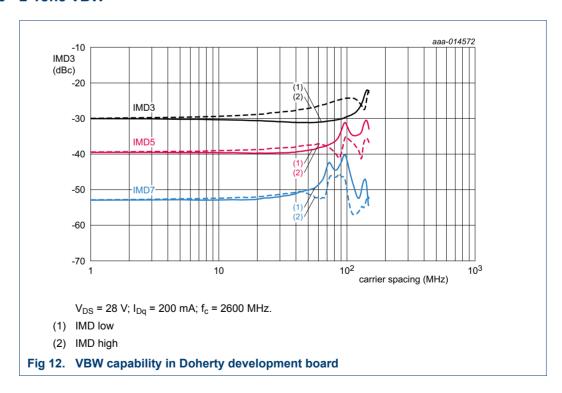
Fig 10. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



- (1) f = 2496 MHz
- (2) f = 2690 MHz

Fig 11. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

7.6.3 2-Tone VBW



8. Package outline

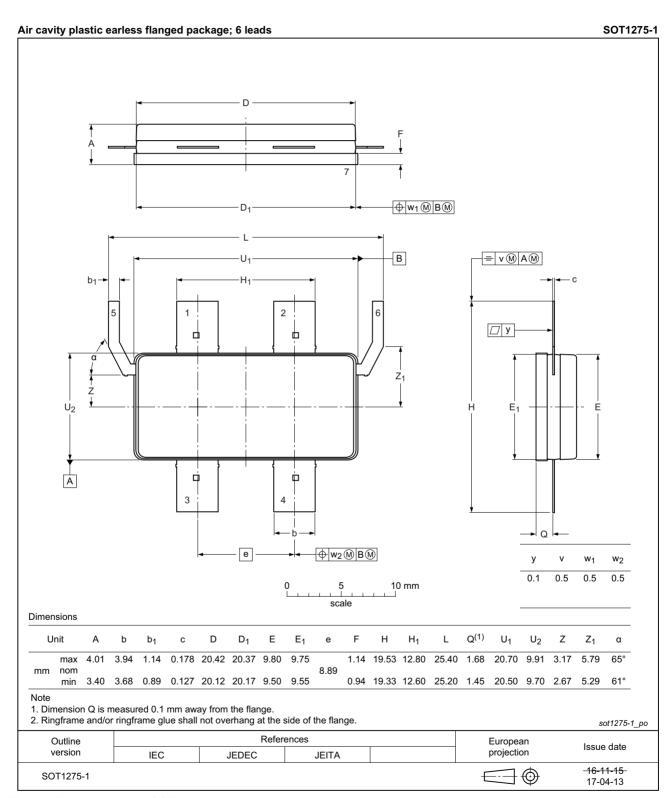


Fig 13. Package outline SOT1275-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface-Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC8G27LS-180AV v.5	20170524	Product data sheet	-	BLC8G27LS-180AV v.4
Modifications:	Table 2 on p	page 2: change simplified	outline	-
	• Table 3 on page 2: change version to SOT1275-1			
	• Figure 13 or	n page 10: change packa	ge outline drawing to	SOT1275-1
BLC8G27LS-180AV v.4	20161202	Product data sheet	-	BLC8G27LS-180AV v.3
BLC8G27LS-180AV v.3	20150901	Product data sheet	-	BLC8G27LS-180AV v.2
BLC8G27LS-180AV v.2	20150209	Product data sheet	-	BLC8G27LS-180AV v.1
BLC8G27LS-180AV v.1	20140701	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Power LDMOS transistor

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BLC8G27LS-180AV

Power LDMOS transistor

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Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.